# MicroCapacitance (MC) SA SIDACtor Device



The DO-214AA SA MC *SIDACtor* series is intended for applications sensitive to load values. Typically, high speed connections require a lower capacitance.  $C_0$  values for the MicroCapacitance device are 40% lower than a standard SA part.

This MC *SIDACtor* series is used to enable equipment to meet various regulatory requirements including GR 1089, ITU K.20, K.21, and K.45, IEC 60950, UL 60950, and TIA-968-A (formerly known as FCC Part 68).

#### **Electrical Parameters**

Part Number *	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>T</sub> Volts	I <sub>DRM</sub> μAmps	I <sub>S</sub> mAmps	I <sub>T</sub> Amps	I <sub>H</sub> mAmps	C <sub>O</sub> pF
P0080SA MC	6	25	4	5	800	2.2	50	45
P0300SA MC	25	40	4	5	800	2.2	50	25

<sup>\*</sup> For surge ratings, see table below.

#### General Notes:

- All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.
- IPP is a repetitive surge rating and is guaranteed for the life of the product.
- · Listed SIDACtor devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.
- V<sub>DRM</sub> is measured at I<sub>DRM</sub>.
- V<sub>S</sub> is measured at 100 V/µs.
- Special voltage (V<sub>S</sub> and V<sub>DRM</sub>) and holding current (I<sub>H</sub>) requirements are available upon request.
- Off-state capacitance (C<sub>O</sub>) is measured at 1 MHz with a 2 V bias.

## Surge Ratings

Series	I <sub>PP</sub> 2x10 µs Amps	I <sub>PP</sub> 8x20 μs Amps	I <sub>PP</sub> 10x160 μs Amps	I <sub>PP</sub> 10x560 μs Amps	I <sub>PP</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
Α	150	150	90	50	45	20	500

t<sub>r</sub> = rise time to peak value t<sub>d</sub> = decay time to half value

Half Value

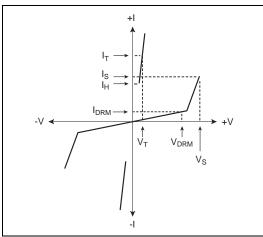
t - Time (µs)

Peak

Value Waveform =  $t_r \times t_d$ 

### **Thermal Considerations**

Package	Symbol	Parameter	Value	Unit
DO-214AA	TJ	Operating Junction Temperature Range	-40 to +150	°C
	TS	Storage Temperature Range	-65 to +150	°C
	$R_{ hetaJA}$	Thermal Resistance: Junction to Ambient	90	°C/W



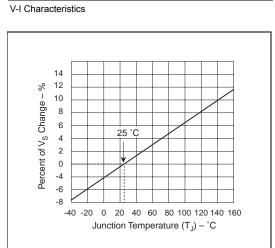
 $t_{r}$  x  $t_{d}$  Pulse Wave-form

Ipp - Peak Pulse Current - %Ipp

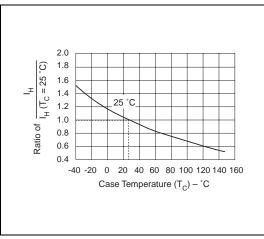
100

50

0 L



Normalized V<sub>S</sub> Change versus Junction Temperature



Normalized DC Holding Current versus Case Temperature